

REMARKS/ARGUMENTS**1. Rejection of claim 1 and claim 10 under 35 U.S.C. 102 (b) as being anticipated by Applicant's admitted prior art (AAPA):**

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Clam 1 is amended to overcome this rejection. Specifically, "a passivation layer formed on the dielectric layer to completely cover the dielectric layer" is added. Therefore, the dielectric layer 48 in the present application is significantly corresponding to the dielectric layer 18 in AAPA, and the passivation layer 50 in the present application is corresponding to the passivation layer 26 in AAPA. According to the amended claim 1, the passivation layer 50 is on the dielectric layer 48 to completely cover the dielectric layer 48. However, in AAPA, the dielectric layer 18 is covered not only by the passivation layer 26, but also by a metal pad 24. That means, in AAPA, the passivation layer 26 dose not completely cover the dielectric layer 18.

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In addition, "an under bump metallurgy layer (UBM layer) formed on the dielectric layer" is revised to "an under bump metallurgy layer (UBM layer) directly formed on the dielectrie surface of the passivation layer without a metal pad there in between", so as to emphasis the differences between the present application and the AAPA, in which the UBM layer 28 is formed on a metal pad 24.

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Similarly, in the claim 10, the formation of a passivation layer, which was defined as part of a dielectric layer, is specifically described. According to the amended claim 10, "forming a passivation layer 50 on the surface of the dielectric layer to completely cover the dielectric layer 48" is added. However, in AAPA, the passivation layer 26 is not formed to completely cover the dielectric layer 18. In other words, the dielectric layer 18 is covered not only by the passivation layer 26, but also by a metal pad 24.

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Moreover, "performing an UBM process to form at least one UBM layer to cover both on the metal pad within the first area and at least one UBM layer on to cover portions of the dielectric layer within the second area" is revised to "performing an UBM process to form at least one UBM layer on the metal pad within the first area and at

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least one UBM layer directly on the surface of the passivation layer without a metal pad there in between within the second area” to emphasis the differences between the present application and the AAPA, in which the UBM layer 28 is formed on a metal pad 24 rather than the passivation layer 26. Therefore, the present application is
5 different from AAPA.

No new matter is introduced by the above amendments. Reconsideration of claim 1 and claim 10 is politely requested.

10 **2. Rejection of claims 2, 4-11,13-18 under 35 U.S.C. 102 (b) as being anticipated by Applicant’s admitted prior art (AAPA):**

Claim 11 is canceled. Claims 2,4-9 are dependent on claim 1, and should be allowed if claim 1 is allowed. Similarly, claims 13-18 are dependent on claim 10, and should be allowed if claim 10 is allowed. Reconsideration of claims 2, 4-9,13-18 is therefore
15 politely requested.

3. Rejection of claims 3, 12 under 35 U.S.C. 103 (a) as being unpatentable over Applicant’s admitted prior art (AAPA) in view Owada et al.:

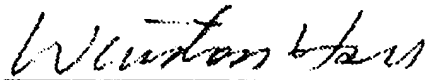
Claim 3 is dependent on claim 1, and should be allowed if claim 1 is allowed.
20 Similarly, claim 12 is dependent on claim 10, and should be allowed if claim 10 is allowed. Reconsideration of claims 3, 12 is therefore politely requested.

Applicant respectfully requests that a timely Notice of Allowance be issued in this case.

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Respectfully submitted,



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- 10 Note: Please leave a message in my voice mail if you need to talk to me. The time in D.C. is 12 hours behind the Taiwan time, i.e. 9 AM in D.C. = 9 PM in Taiwan.